

HSU119

Silicon Epitaxial Planar Diode for High Speed Switching

HITACHI

ADE-208-444(Z)

Rev 0

Feb. 1997

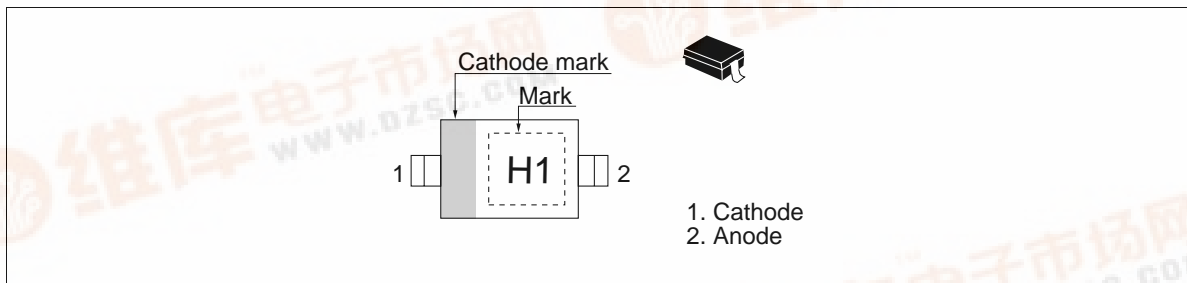
Features

- Low capacitance. ($C = 2.0\text{pF max}$)
- Short reverse recovery time. ($t_r = 3.0\text{ns max}$)
- Ultra small Resin Package (URP) is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HSU119	H1	URP

Outline



HSU119

Absolute Maximum Ratings (Ta = 25°C)

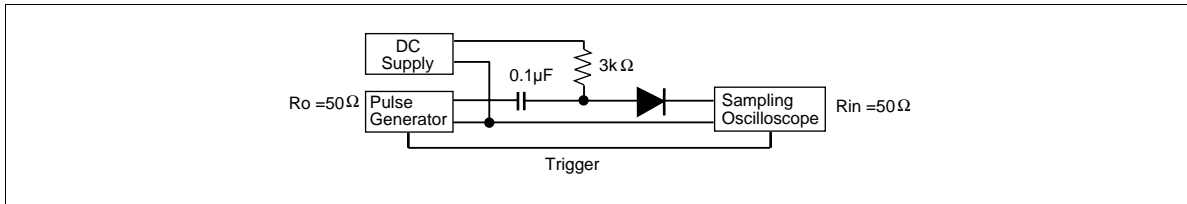
Item	Symbol	Value	Unit
Peak reverse voltage	V_{RM}	85	V
Reverse voltage	V_R	80	V
Average forward current	I_O	100	mA
Peak rectified current	I_{FM}	300	mA
Non-Repetitive peak forward surge current	I_{FSM}^{*1}	4	A
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-55 to +125	°C

Note: 1. Within 1μ s forward surge current.

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_{F1}	—	—	0.8	V	$I_F = 10\text{ mA}$
	V_{F2}	—	—	1.2		$I_F = 100\text{ mA}$
Reverse current	I_R	—	—	0.1	μA	$V_R = 80\text{ V}$
Capacitance	C	—	—	2.0	pF	$V_R = 0\text{ V}, f = 1\text{ MHz}$
Reverse recovery time ^{*1}	t_{rr}	—	—	3.0	ns	$I_F = 10\text{ mA}, V_R = 6\text{ V}, R_L = 50\Omega$

Note: 1. Reverse recovery time test circuit



Main Characteristic

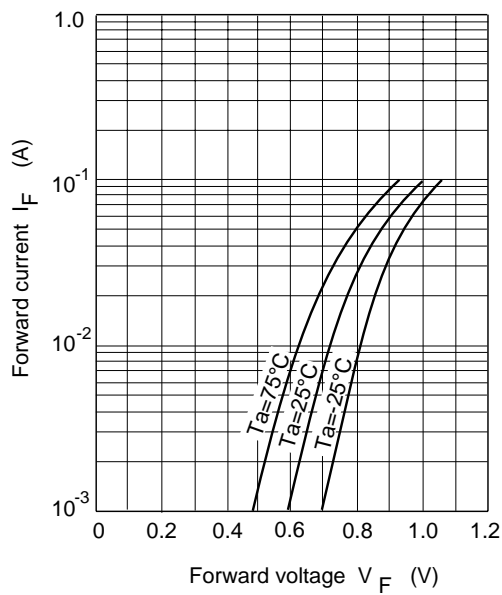


Fig.1 Forward current Vs. Forward voltage

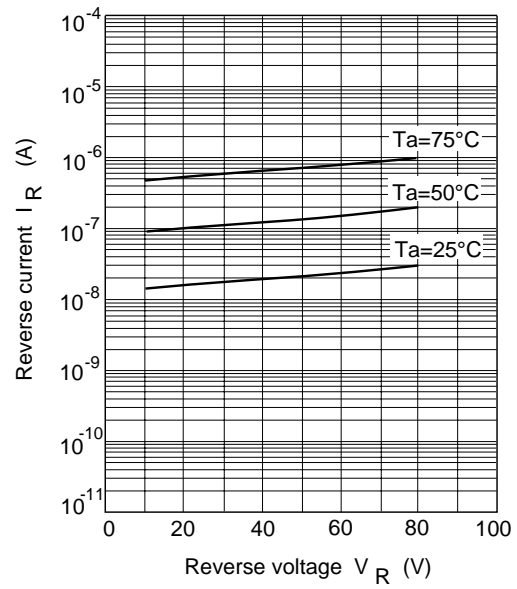


Fig.2 Reverse current Vs. Reverse voltage

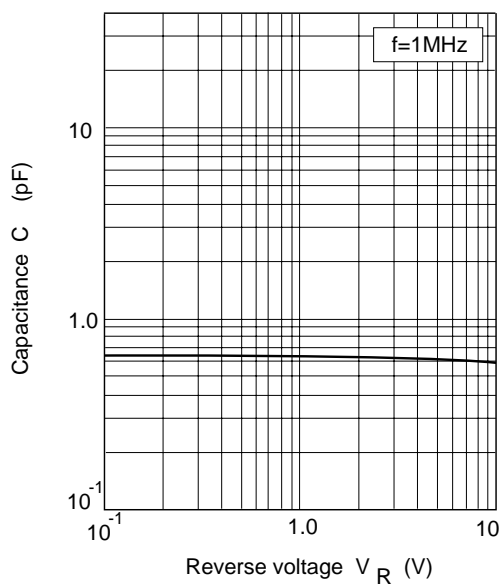
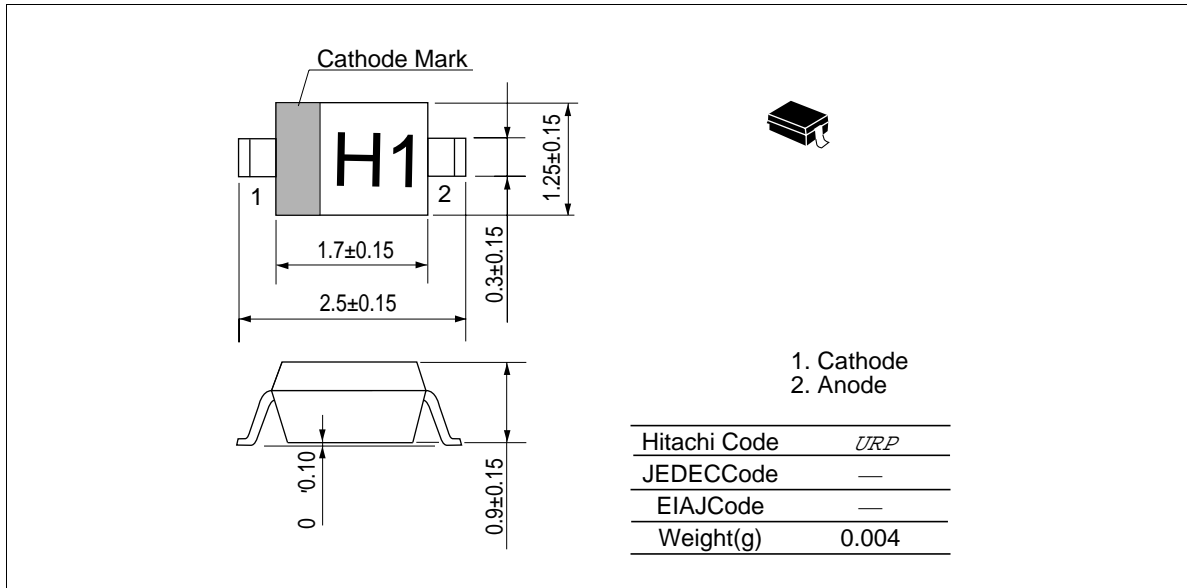


Fig.3 Capacitance Vs. Reverse voltage

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Package Dimensions

Unit : mm



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